Vincotech

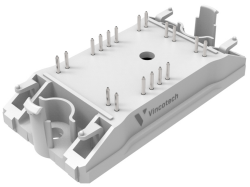
10-FZ07B2A042UF-PB53L98
datasheet

***flow*BOOST 0 dual SiC** **650 V / 42 mΩ**

Features

- High efficiency dual booster
- Low Inductance Layout
- Ultra fast switching frequency
- Integrated temperature sensor

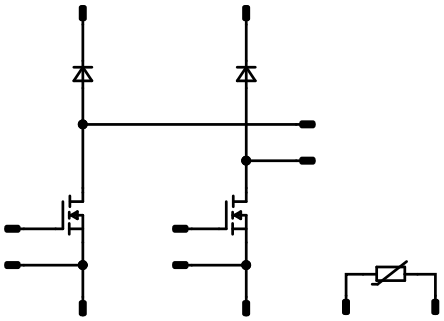
flow 0 12 mm housing



Target applications

- Power Supply
- Solar Inverters

Schematic



Types

- 10-FZ07B2A042UF-PB53L98

Maximum Ratings

T_j = 25 °C, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Boost Switch				
Drain-source voltage	V_{DSS}		650	V
Drain current (DC current)	I_D	$T_j = T_{jmax}$ T_s = 80 °C	24	A
Peak drain current	I_{DM}	t_p limited by T_{jmax}	125	A
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	38	W
Gate-source voltage	V_{GSS}		±25	V
Maximum Junction Temperature	T_{jmax}		175	°C
Boost Diode				
Peak repetitive reverse voltage	V_{RRM}		650	V
Forward current (DC current)	I_F	$T_j = T_{jmax}$ T_s = 80 °C	28	A
Repetitive peak forward current	I_{FRM}	t_p limited by T_{jmax}	92	A
Surge (non-repetitive) forward current	I_{FSM}	Single Half Sine Wave, t_p = 10 ms	180	A
Surge current capability	I^2t		162	A^2s
Total power dissipation	P_{tot}	$T_j = T_{jmax}$ T_s = 80 °C	60	W
Maximum junction temperature	T_{jmax}		175	°C
Module Properties				
Thermal Properties				
Storage temperature	T_{stg}		-40…+125	°C
Operation temperature under switching condition	T_{jop}		-40…+(T_{jmax} - 25)	°C
Isolation Properties				
Isolation voltage	V_{isol}	DC Test Voltage* t_p = 2 s	6000	V
Isolation voltage	V_{isol}	AC Voltage t_p = 1 min	2500	V
Creepage distance			>12,7	mm
Clearance			9,1	mm
Comparative Tracking Index	CTI		≥ 200	

*100 % tested in production

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Switch										
Static										
Drain-source on-state resistance	$r_{DS(on)}$		12		30	25 125 150		43 60 67	52(1)	mΩ
Gate-source threshold voltage	$V_{GS(th)}$		0		0,01	25	4	5	6	V
Gate to Source Leakage Current	I_{GSS}		20	0		25		6	20	µA
Zero Gate Voltage Drain Current	I_{DSS}		0	650		25		0,7	150	µA
Internal gate resistance	r_g							4,5		Ω
Gate charge	Q_g		-5/12	400	30	25		43		nC
Short-circuit input capacitance	C_{iss}	f = 100 kHz	0	100	0	25		1500		pF
Short-circuit output capacitance	C_{oss}							200		
Reverse transfer capacitance	C_{rss}							2,2		
Diode forward voltage	V_{SD}		0		20	25		1,5	1,75	V
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						2,49		K/W
Dynamic										
Turn-on delay time	$t_{d(on)}$	R_{gon} = 4 Ω R_{goff} = 4 Ω	0/12	400	40	25 125 150		18,88 18,56 18,24		ns
Rise time	t_r					25 125 150		6,08 5,44 5,44		ns
Turn-off delay time	$t_{d(off)}$					25 125 150		37,12 37,12 37,76		ns
Fall time	t_f					25 125 150		7,54 4,85 5,18		ns
Turn-on energy (per pulse)	E_{on}	Q_{rFWD}=0,063 µC Q_{rFWD}=0,064 µC Q_{rFWD}=0,062 µC				25 125 150		0,148 0,122 0,124		mWs
Turn-off energy (per pulse)	E_{off}					25 125 150		0,075 0,052 0,056		mWs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Boost Diode										
Static										
Forward voltage	V_F				20	25 125 150		1,47 1,67 1,75	1,8(1)	V
Reverse leakage current	I_R	V_r = 650 V				25		24	120	µA
Thermal										
Thermal resistance junction to sink (2)	$R_{th(j-s)}$	λ_{paste} = 3,4 W/mK (PSX)						1,58		K/W
Dynamic										
Peak recovery current	I_{RRM}	di/dt=5311 A/µs di/dt=6589 A/µs di/dt=6502 A/µs	0/12	400	40	25 125 150		18,9 20,79 21,11		A
Reverse recovery time	t_{rr}					25 125 150		7,58 7,73 7,74		ns
Recovered charge	Q_r					25 125 150		0,063 0,064 0,062		µC
Reverse recovered energy	E_{rec}					25 125 150		$5{,}851 \times 10^{-3}$ 0,014 0,014		mWs
Peak rate of fall of recovery current	$(di_{rf}/dt)_{max}$					25 125 150		6414 7432 7310		A/µs

Characteristic Values

Parameter	Symbol	Conditions					Values			Unit
			V_{GE} [V] V_{GS} [V]	V_{CE} [V] V_{DS} [V] V_F [V]	I_C [A] I_D [A] I_F [A]	T_j [°C]	Min	Typ	Max	
Thermistor										
Static										
Rated resistance	R					25		22		kΩ
Deviation of R_{100}	$\Delta_{R/R}$	R_{100} = 1484 Ω				100	-5		5	%
Power dissipation	P							5		mW
Power dissipation constant	d					25		1,5		mW/K
B-value	$B_{(25/50)}$	Tol. ±1 %						3962		K
B-value	$B_{(25/100)}$	Tol. ±1 %						4000		K
Vincotech Thermistor Reference									I	

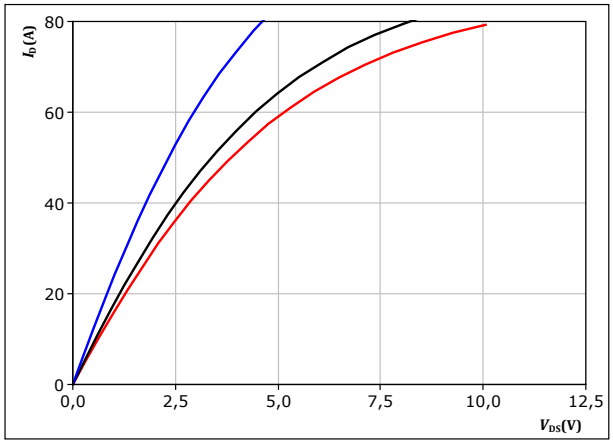
(1) Value at chip level
(2) Only valid with pre-applied Vincotech thermal interface material.

Boost Switch Characteristics

figure 1. MOSFET

Typical output characteristics

$I_D = f(V_{DS})$

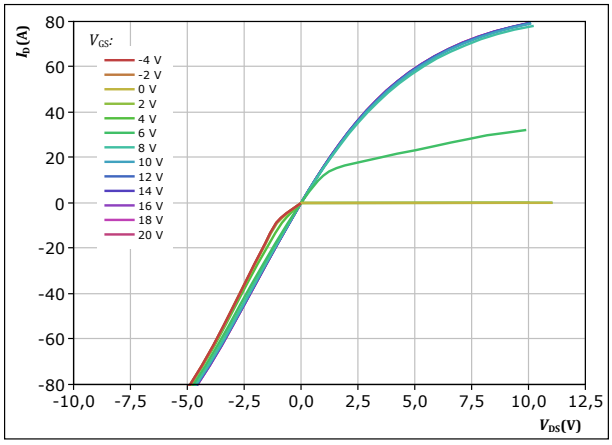


t_p =	250	µs		
V_{GS} =	12	V	T_j:	25 °C
				125 °C
				150 °C

figure 2. MOSFET

Typical output characteristics

$I_D = f(V_{DS})$



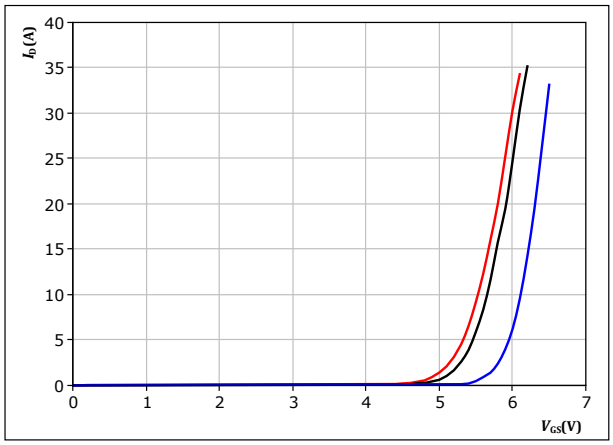
t_p =	250	µs
T_j =	150	°C

V_{GS} from -4 V to 20 V in steps of 2 V

figure 3. MOSFET

Typical transfer characteristics

$I_D = f(V_{GS})$

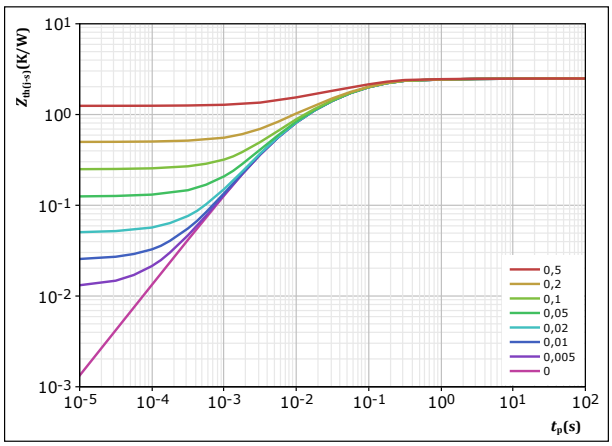


t_p =	250	µs		
V_{DS} =	10	V	T_j:	25 °C
				125 °C
				150 °C

figure 4. MOSFET

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D =	t_p / T	
$R_{th(j-s)}$ =	2,494	K/W

MOSFET thermal model values

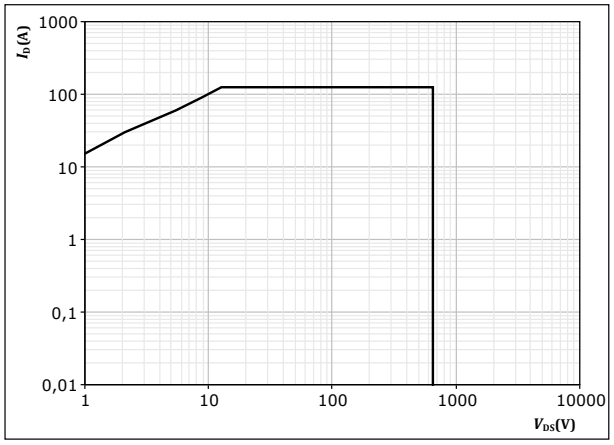
R (K/W)	τ (s)
3,22E-02	9,01E+00
9,03E-02	1,04E+00
1,04E+00	9,78E-02
8,96E-01	2,16E-02
4,53E-01	4,76E-03
-1,36E-02	9,57E-04

Boost Switch Characteristics

figure 5. **MOSFET**

Safe operating area

$I_D = f(V_{DS})$

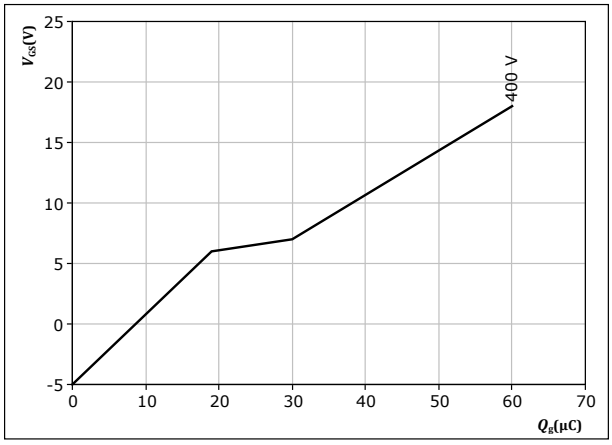


$D =$ single pulse
$T_s =$ 80 °C
$V_{GS} =$ 12 V
$T_j =$ T_{jmax}

figure 6. **MOSFET**

Gate voltage vs gate charge

$V_{GS} = f(Q_g)$



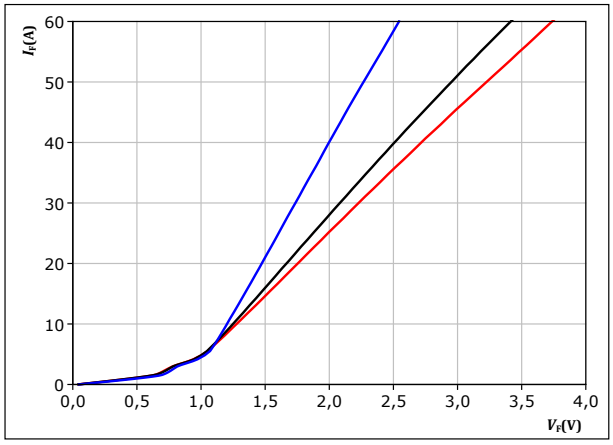
$I_D =$ 30 A
$T_j =$ 25 °C

Boost Diode Characteristics

figure 7. **FWD**

Typical forward characteristics

$I_F = f(V_F)$



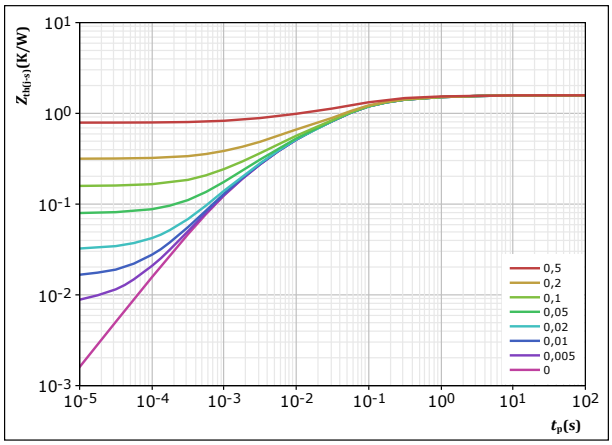
t_p = 250 µs

T_j: 25 °C, 125 °C, 150 °C

figure 8. **FWD**

Transient thermal impedance as a function of pulse width

$Z_{th(j-s)} = f(t_p)$



D = t_p / T

$R_{th(j-s)}$ = 1,58 K/W

FWD thermal model values

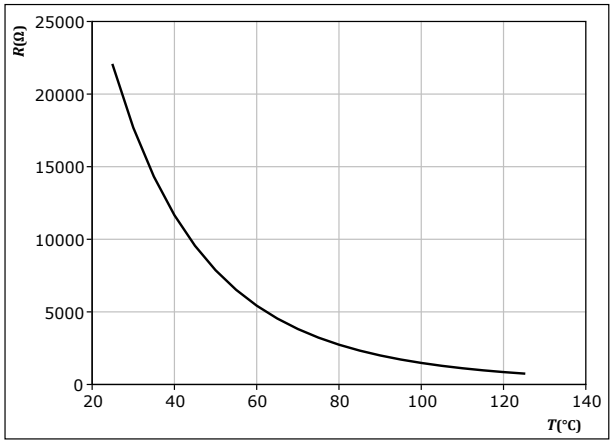
R (K/W)	τ (s)
8,96E-02	2,60E+00
2,36E-01	2,99E-01
8,04E-01	5,52E-02
3,49E-01	6,69E-03
1,01E-01	1,09E-03

Thermistor Characteristics

figure 9. **Thermistor**

Typical NTC characteristic as function of temperature

$R_T = f(T)$

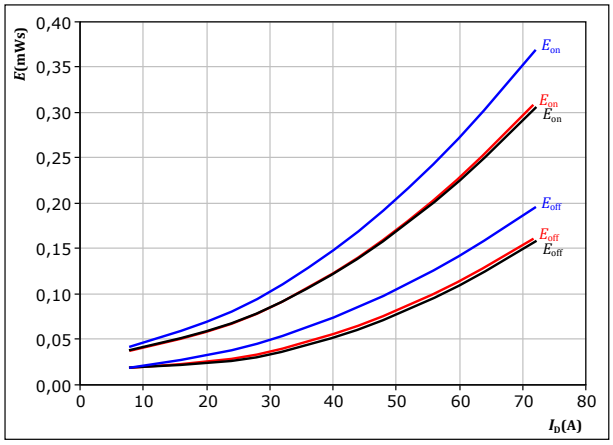


Boost Switching Characteristics

figure 10. **MOSFET**

Typical switching energy losses as a function of drain current

$E = f(I_D)$



With an inductive load at

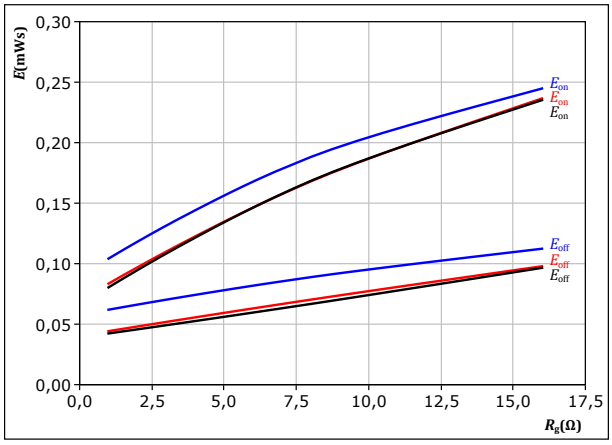
V_{DS} =	400	V
V_{GS} =	0/12	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 11. **MOSFET**

Typical switching energy losses as a function of gate resistor

$E = f(R_g)$



With an inductive load at

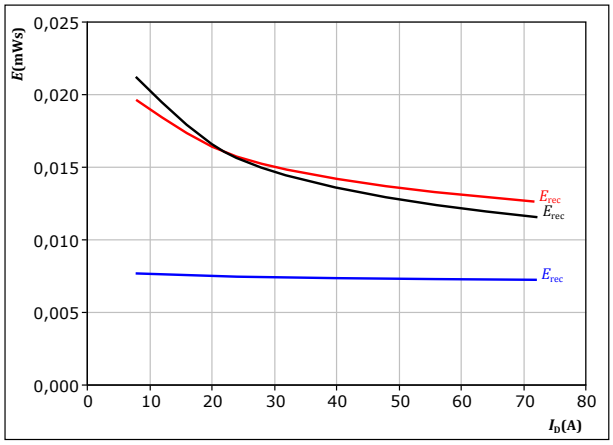
V_{DS} =	400	V
V_{GS} =	0/12	V
I_D =	40	A

T_j: 25 °C, 125 °C, 150 °C

figure 12. **FWD**

Typical reverse recovered energy loss as a function of drain current

$E_{rec} = f(I_D)$



With an inductive load at

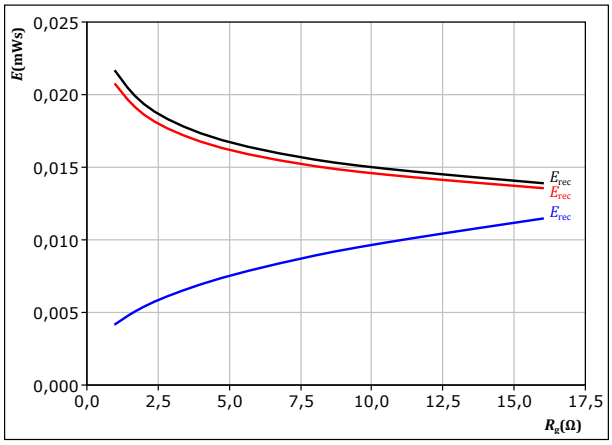
V_{DS} =	400	V
V_{GS} =	0/12	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 13. **FWD**

Typical reverse recovered energy loss as a function of gate resistor

$E_{rec} = f(R_g)$



With an inductive load at

V_{DS} =	400	V
V_{GS} =	0/12	V
I_D =	40	A

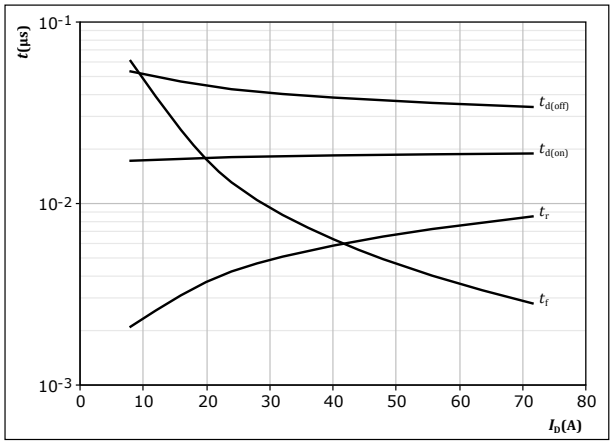
T_j: 25 °C, 125 °C, 150 °C

Boost Switching Characteristics

figure 14. **MOSFET**

Typical switching times as a function of drain current

$t = f(I_D)$



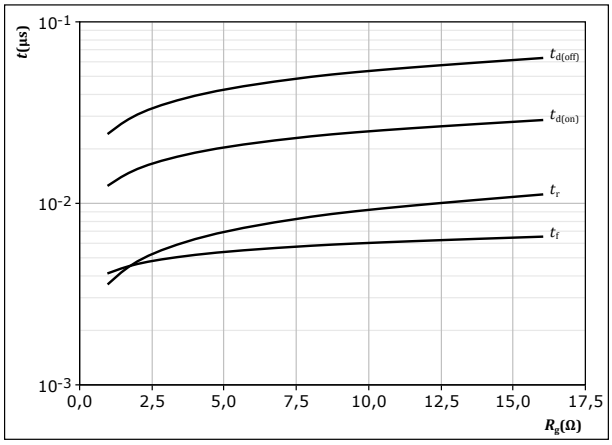
With an inductive load at

T_j =	150	°C
V_{DS} =	400	V
V_{GS} =	0/12	V
R_{gon} =	4	Ω
R_{goff} =	4	Ω

figure 15. **MOSFET**

Typical switching times as a function of gate resistor

$t = f(R_g)$



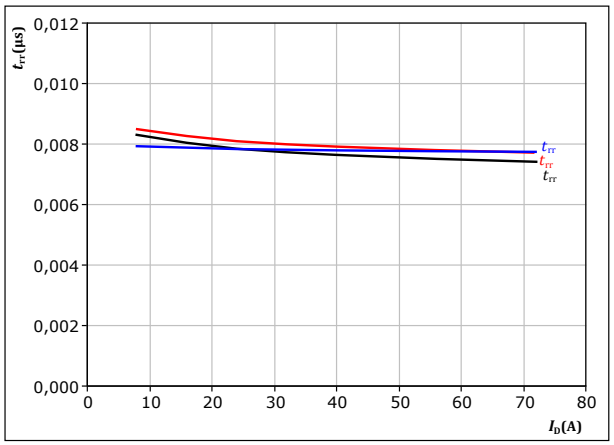
With an inductive load at

T_j =	150	°C
V_{DS} =	400	V
V_{GS} =	0/12	V
I_D =	40	A

figure 16. **FWD**

Typical reverse recovery time as a function of drain current

$t_{rr} = f(I_D)$



At

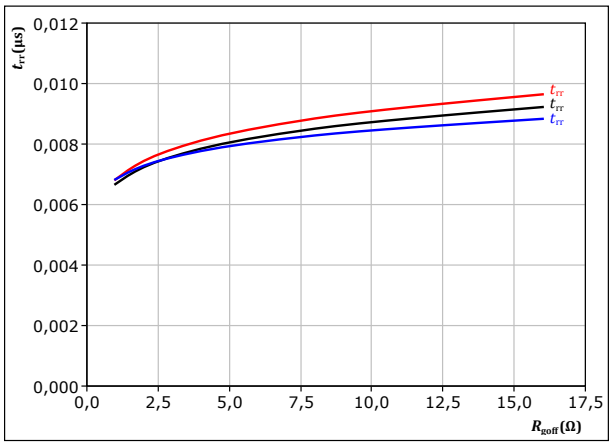
V_{DS} =	400	V
V_{GS} =	0/12	V
R_{gon} =	4	Ω

T_j: 25 °C, 125 °C, 150 °C

figure 17. **FWD**

Typical reverse recovery time as a function of turn off gate resistor

$t_{rr} = f(R_{goff})$



At

V_{DS} =	400	V
V_{GS} =	0/12	V
I_D =	40	A

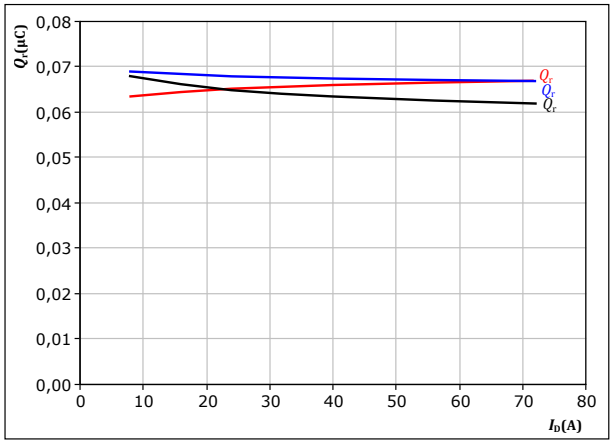
T_j: 25 °C, 125 °C, 150 °C

Boost Switching Characteristics

figure 18. **FWD**

Typical recovered charge as a function of drain current

$Q_r = f(I_D)$

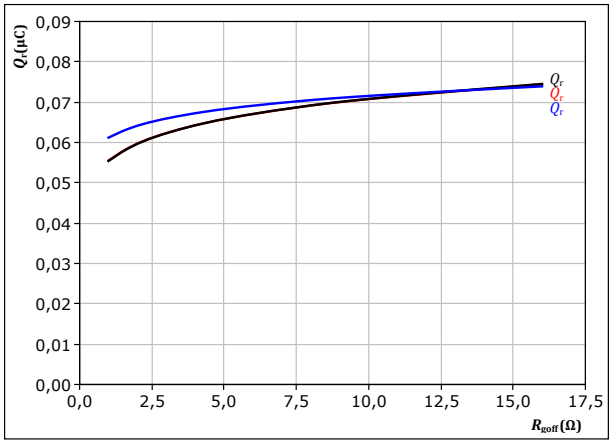


At					
	V_{DS} =	400	V		
	V_{GS} =	0/12	V	T_j:	25 °C, 125 °C, 150 °C
	R_{gon} =	4	Ω		

figure 19. **FWD**

Typical recovered charge as a function of turn off gate resistor

$Q_r = f(R_{goff})$

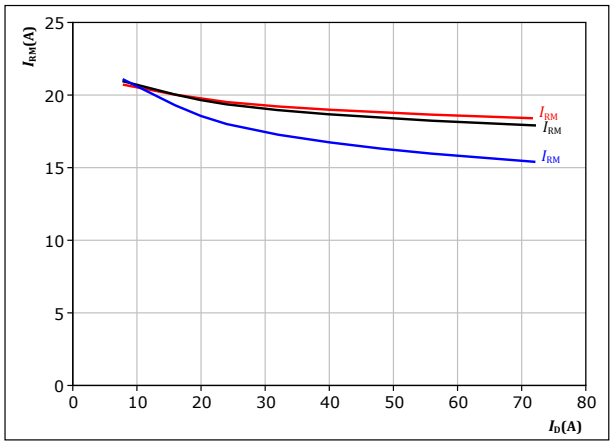


At					
	V_{DS} =	400	V		
	V_{GS} =	0/12	V	T_j:	25 °C, 125 °C, 150 °C
	I_D =	40	A		

figure 20. **FWD**

Typical peak reverse recovery current as a function of drain current

$I_{RM} = f(I_D)$

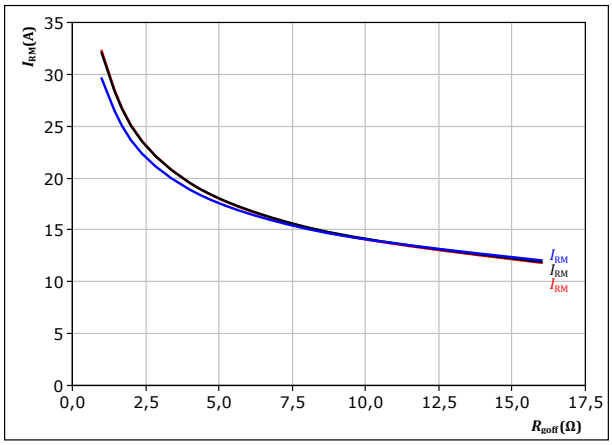


At					
	V_{DS} =	400	V		
	V_{GS} =	0/12	V	T_j:	25 °C, 125 °C, 150 °C
	R_{gon} =	4	Ω		

figure 21. **FWD**

Typical peak reverse recovery current as a function of turn off gate resistor

$I_{RM} = f(R_{goff})$



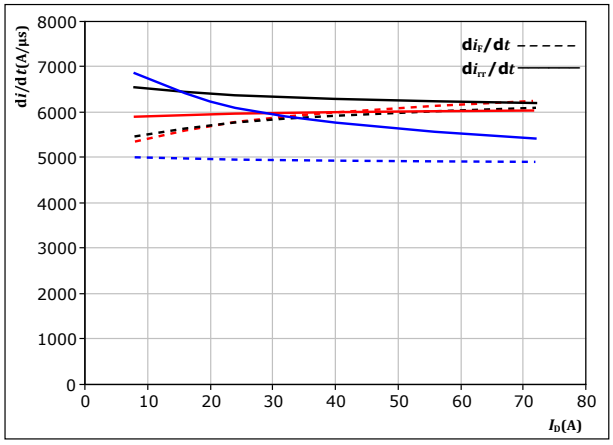
At					
	V_{DS} =	400	V		
	V_{GS} =	0/12	V	T_j:	25 °C, 125 °C, 150 °C
	I_D =	40	A		

Boost Switching Characteristics

figure 22. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of drain current

di_F/dt, di_{rr}/dt = f(I_D)

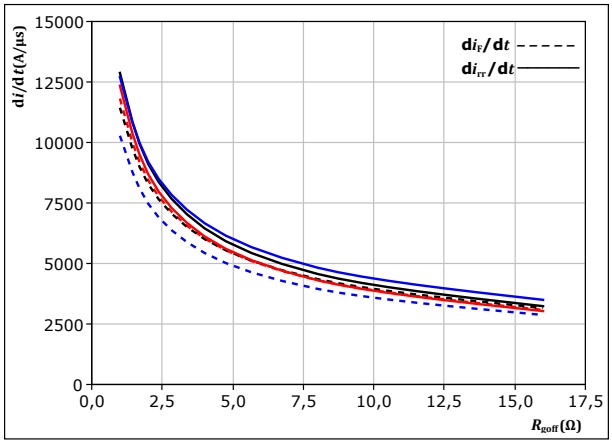


At				
	V_{DS} =	400	V	
	V_{GS} =	0/12	V	
	R_{gon} =	4	Ω	
	T_j:			25 °C
				125 °C
				150 °C

figure 23. **FWD**

Typical rate of fall of forward and reverse recovery current as a function of turn off gate resistor

di_F/dt, di_{rr}/dt = f(R_{goff})

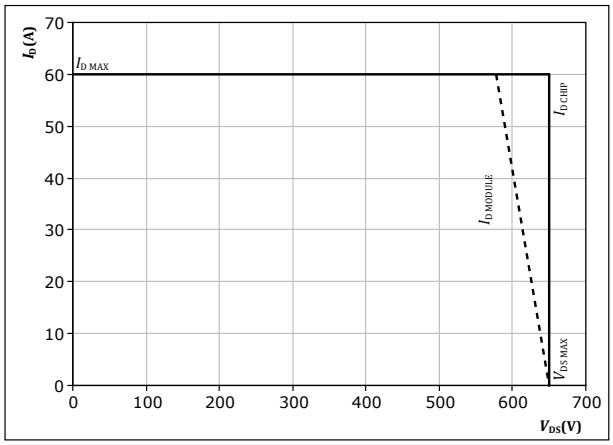


At				
	V_{DS} =	400	V	
	V_{GS} =	0/12	V	
	I_D =	40	A	
	T_j:			25 °C
				125 °C
				150 °C

figure 24. **MOSFET**

Reverse bias safe operating area

I_D = f(V_{DS})



At			
	T_j =	150	°C
	R_{gon} =	4	Ω
	R_{goff} =	4	Ω

Boost Switching Definitions

figure 25. MOSFET

Turn-off Switching Waveforms & definition of t_{doff}, t_{Eoff} (t_{Eoff} = integrating time for E_{off})

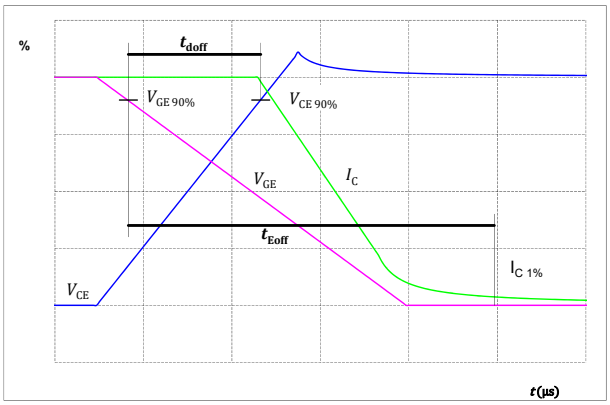


figure 26. MOSFET

Turn-on Switching Waveforms & definition of t_{don}, t_{Eon} (t_{Eon} = integrating time for E_{on})

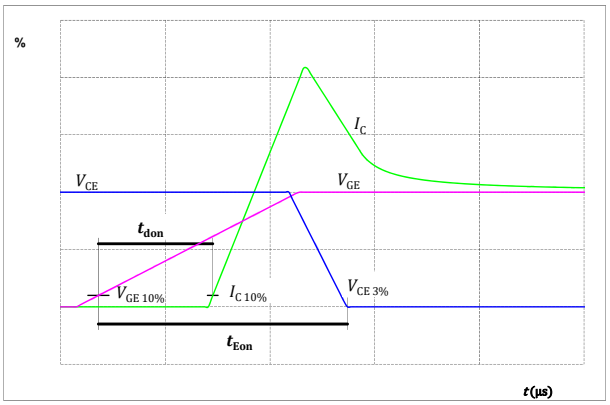


figure 27. MOSFET

Turn-off Switching Waveforms & definition of t_f

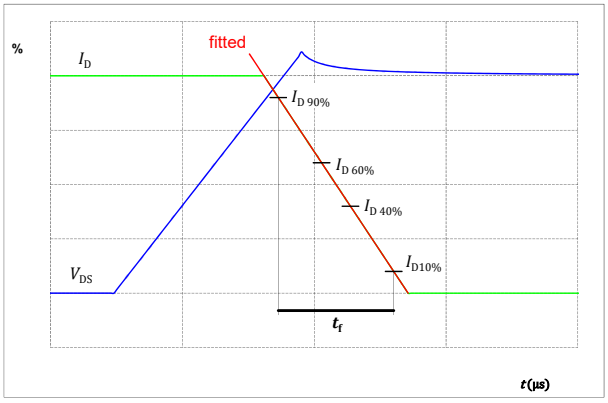
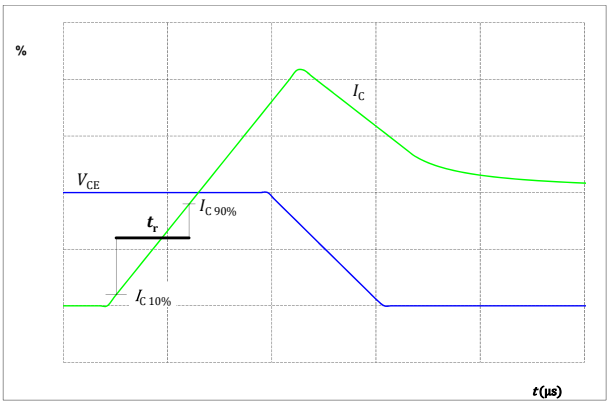


figure 28. MOSFET

Turn-on Switching Waveforms & definition of t_r



Boost Switching Definitions

figure 29. **FWD**

Turn-off Switching Waveforms & definition of t_{trr}

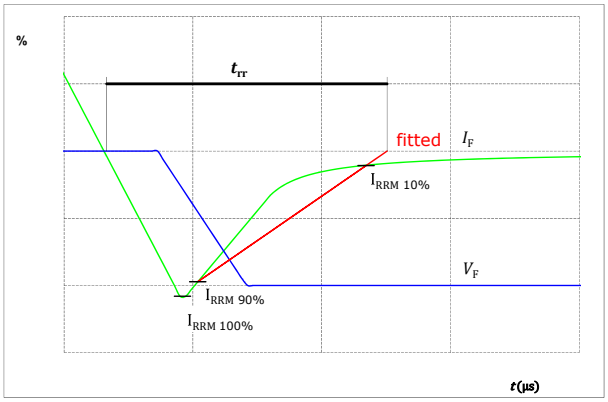


figure 30. **FWD**

Turn-on Switching Waveforms & definition of t_{Qrr} (t_{Qrr} = integrating time for Q_{rr})

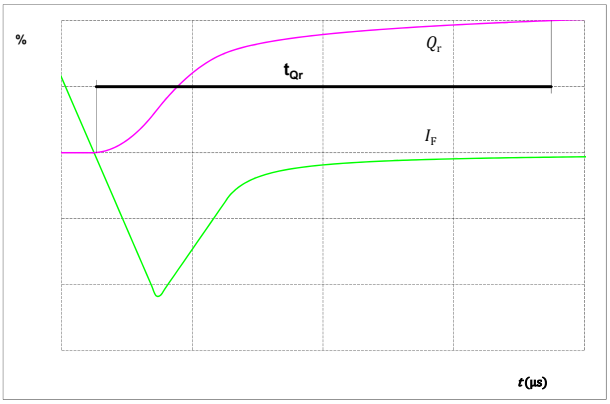
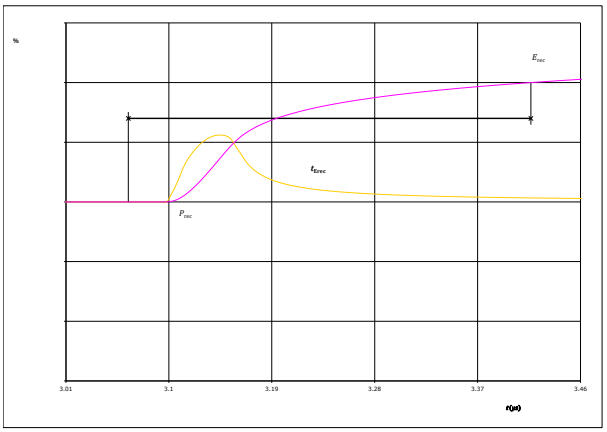


figure 31. **FWD**

Turn-on Switching Waveforms & definition of t_{Erec} (t_{Erec} = integrating time for E_{rec})



Ordering Code

Version	Ordering Code
Without thermal paste	10-FZ07B2A042UF-PB53L98
With thermal paste (5,2 W/mK, PTM6000HV)	10-FZ07B2A042UF-PB53L98-/7/
With thermal paste (3,4 W/mK, PSX-P7)	10-FZ07B2A042UF-PB53L98-/3/

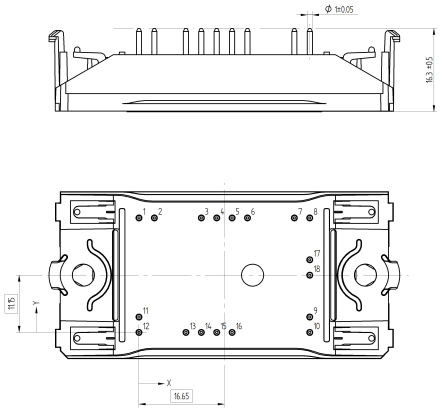
Marking

	Name		Date code	UL & VIN	Lot	Serial
Text	NN-NNNNNNNNNNNNN-TTTTTTVV		WWYY	UL VIN	LLLLL	SSSS
Datamatrix	**Type&Ver**	**Lot number**	**Serial**	**Date code**		
	TTTTTTVV	LLLLL	SSSS	WWYY		

Outline

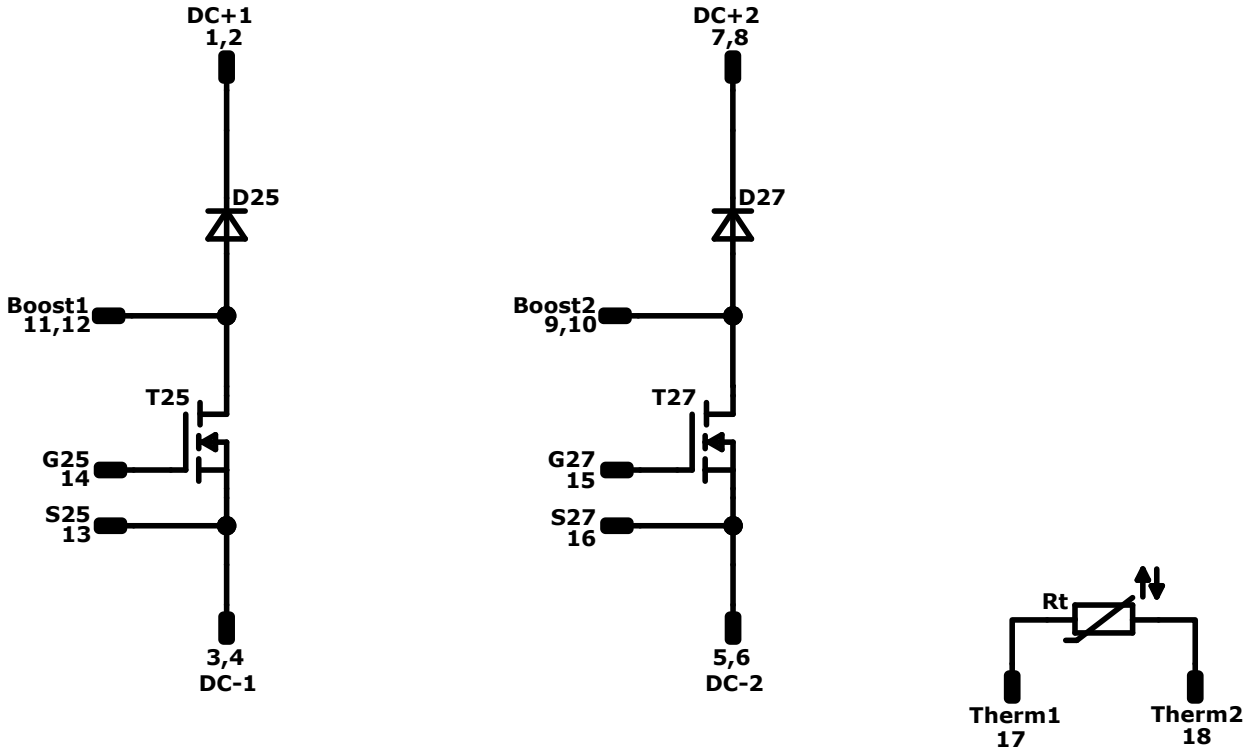
Pin table [mm]

Pin	X	Y	Function
1	0	22,3	DC+1
2	3	22,3	DC+1
3	12,15	22,3	DC-1
4	15,15	22,3	DC-1
5	18,15	22,3	DC-2
6	21,15	22,3	DC-2
7	30,3	22,3	DC+2
8	33,3	22,3	DC+2
9	33,3	3	Boost2
10	33,3	0	Boost2
11	0	3	Boost1
12	0	0	Boost1
13	9,15	0	S25
14	12,15	0	G25
15	15,15	0	G27
16	18,15	0	S27
17	33,3	14,15	Therm1
18	33,3	11,15	Therm2



Tolerance of pinpositions: ±0,5mm at the end of pins
Dimension of coordinate axis is only offset without tolerance

Pinout



Identification

ID	Component	Voltage	Current	Function	Comment
T25, T27	MOSFET	650 V	42 mΩ	Boost Switch	
D25, D27	FWD	650 V	20 A	Boost Diode	
Rt	Thermistor			Thermistor	

Packaging instruction				
Standard packaging quantity (SPQ) 135	>SPQ	Standard	<SPQ	Sample

Handling instruction
Handling instructions for *flow* 0 packages see vincotech.com website.

Package data
Package data for *flow* 0 packages see vincotech.com website.

Vincotech thermistor reference
See Vincotech thermistor reference table at vincotech.com website.

UL recognition and file number
This device is certified according to UL 1557 standard, UL file number E192116. For more information see vincotech.com website.

Document No.:	Date:	Modification:	Pages
10-FZ07B2A042UF-PB53L98-D1-14	9 Jul. 2021		